

Computational Materials Design (CMD[®]) Workshop

Spintronic Design Course

Spintronic · Design · Magnetic control II

Materials Design based on band structures

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Outline

- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary

Role of materials in spintronics

Magnetic thin films

Spin-related properties

- Magnetization
- Perpendicular MA
- Magnetic (tunnel) resistivity
- Spin (Hall) current
- Spin Seebeck/peltier effect
- Spin (orbital) torque
- ...

Spintronic devices

- HDD
- MRAM
- Magnetic domain memory
- Spin microwave/mill-meter wave oscillator
- Spin diode/transistor
- ...

Artificial multilayer thin-films

Required high-performance

Magnetic field

Electric field

Heat

Light

Pressure

External field response

An example of spintronic development

1857 Discovery of Magneto-resistivity

1988 (1995) Giant/Tunneling Magneto-resistivity

2003 FeCoB/MgO-MTJ

2006 MRAM (4Mb) Products

2007 MRAM (256Mb) Products

2007 In-plane MA

2007 Out-of-plane MA (PMA)

2009 Fe/MgO Interfacial PMA

2010 Magnetization switching

By Magnetic field

By current (spin injection)

Role of first principles calculations in materials design

- Quantum mechanics !
- No use of empirical parameters !
- High accuracy in computations !

- Interpretation of experiments
- Understanding
- Prediction with **no restriction of materials**

Unresolved issues

Strong correlated systems, Exited states, etc.

Goal: Prediction of material properties from the periodic table

First principles calculations

①Kohn-Sham equation

$$\left[-\nabla^2 + V_c(\mathbf{r}) + V_{\text{eff}}(\mathbf{r}) \right] \psi_i(\mathbf{r}) = \epsilon_i \psi_i(\mathbf{r})$$

exchange correlation potential $E_{xc}^{\text{LDA}}[n] \approx \int n(\mathbf{r}) \epsilon_{xc}^{\text{LDA}}(n(\mathbf{r}))$

Coulomb potential wave function (basis)

②Total energy

$$E_{\text{total}} = \sum_{i=1}^N \epsilon_i$$

Kohn-Sham eigenvalues (band structure, density of states)

$$-\frac{1}{2} \left[\int V_c(\mathbf{r}) n(\mathbf{r}) d\mathbf{r} + \sum_{\sigma} \int \psi_{\sigma}^{\text{occ}}(\mathbf{r}) (-\nabla^2 \psi_{\sigma}^{\text{occ}}(\mathbf{r})) \psi_{\sigma}^{\text{occ}}(\mathbf{r}) d\mathbf{r} \right] - \frac{1}{2} \sum_{\sigma} Z_{\sigma} V_{c,\sigma}(\mathbf{R}_{\sigma})$$

double counting term

Eigenvalues and eigenstates of electron orbitals in atoms

$$\psi_{nlm}(\mathbf{r}) = R_{nl}(r) Y_{lm}$$

①Orthogonalization in orbitals $\langle \psi_j | \psi_i \rangle = 0$

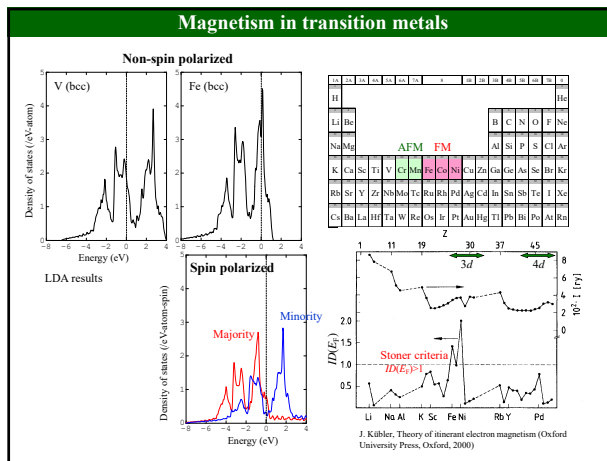
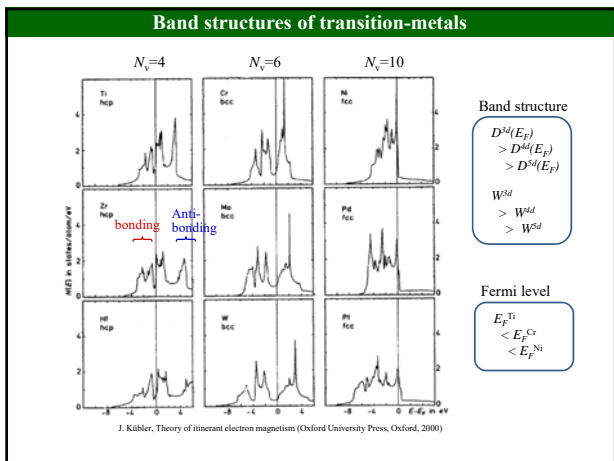
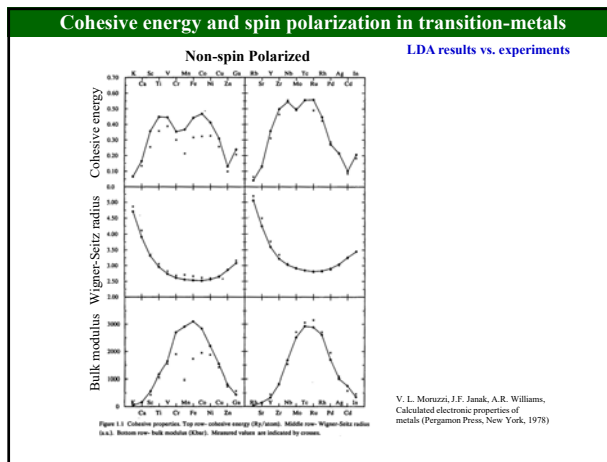
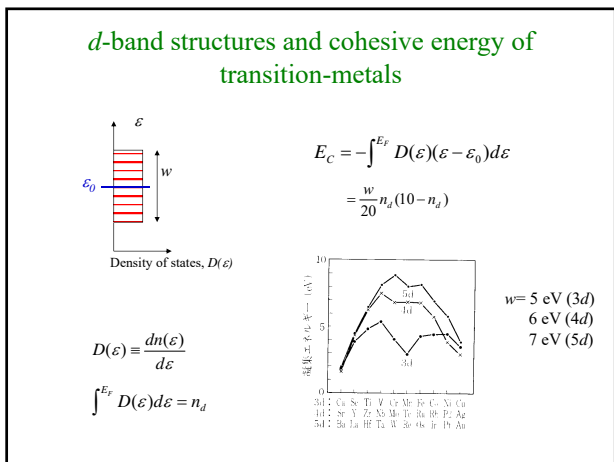
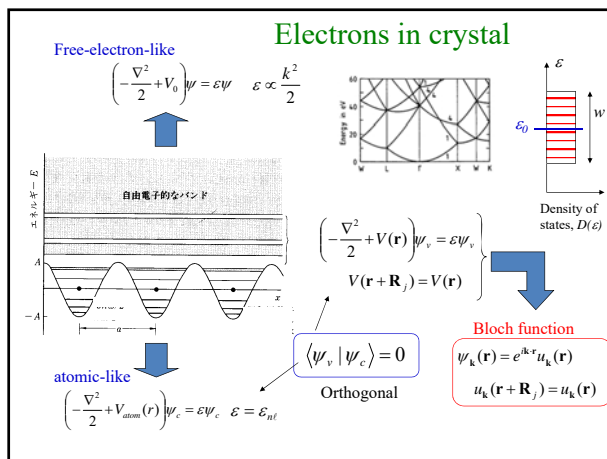
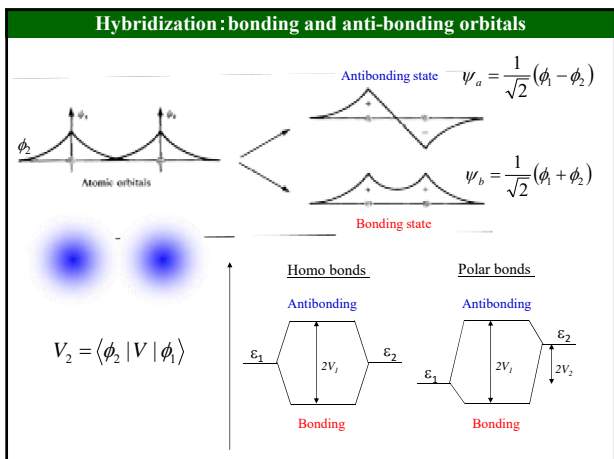
②Spatial spread of wave function Hybridization in crystals

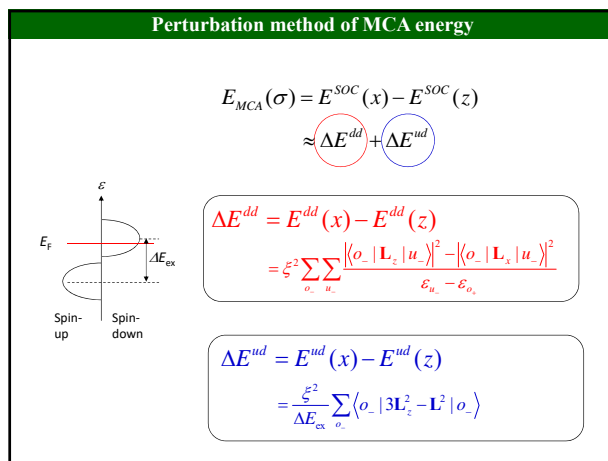
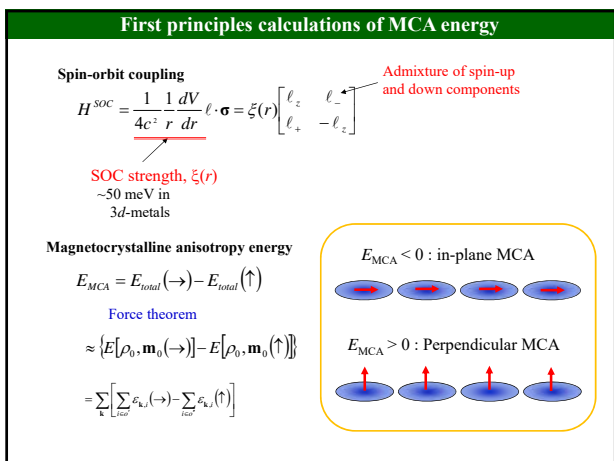
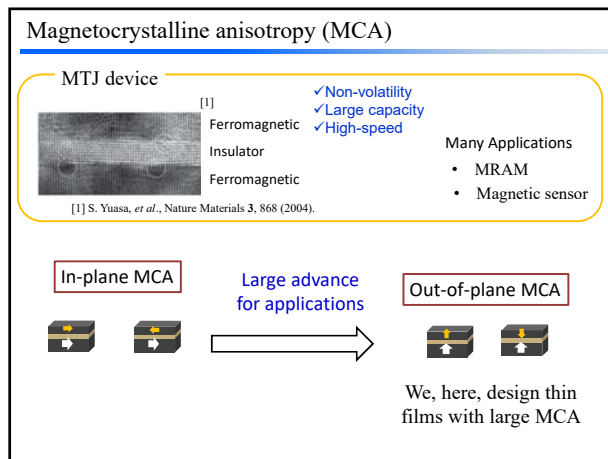
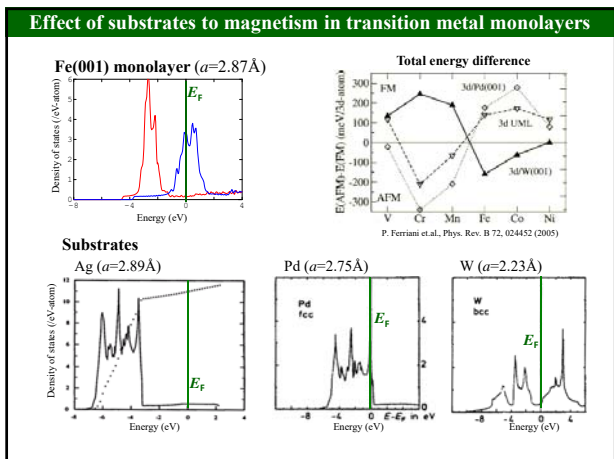
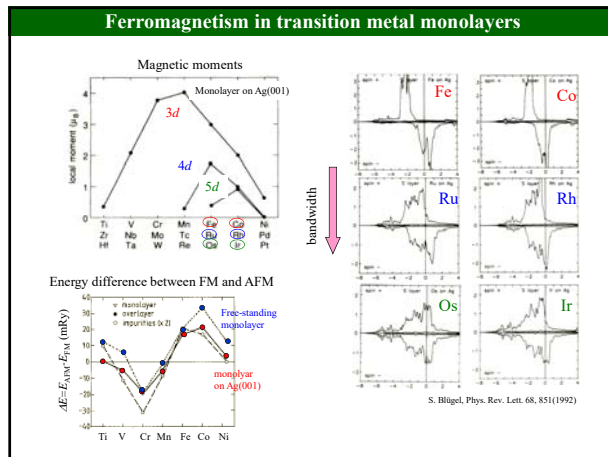
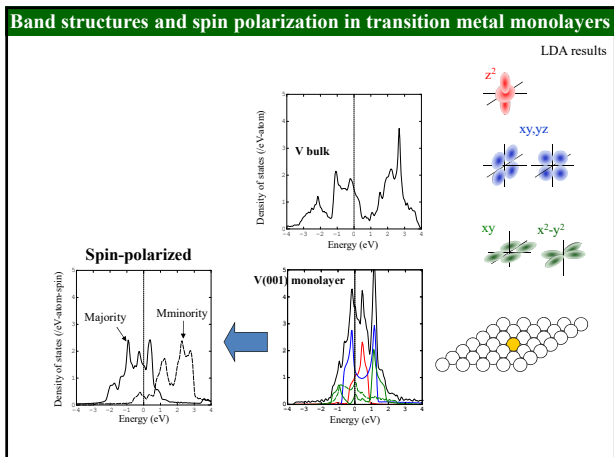
Li : $1s^2 2s$

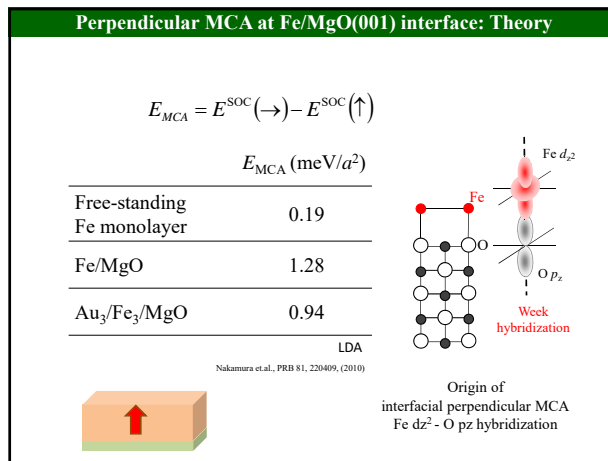
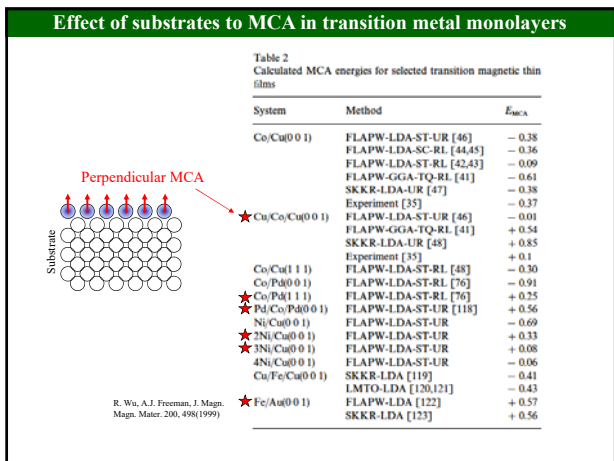
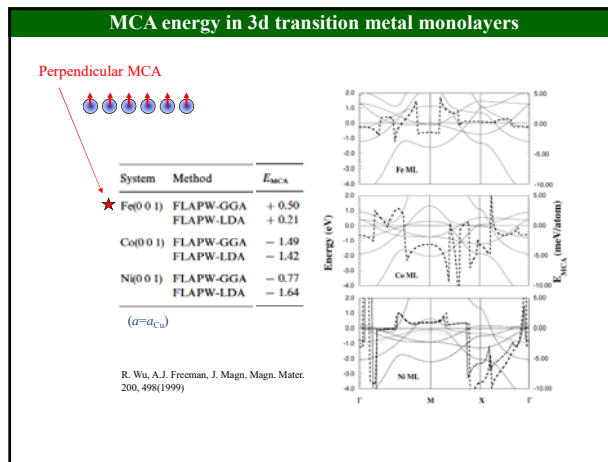
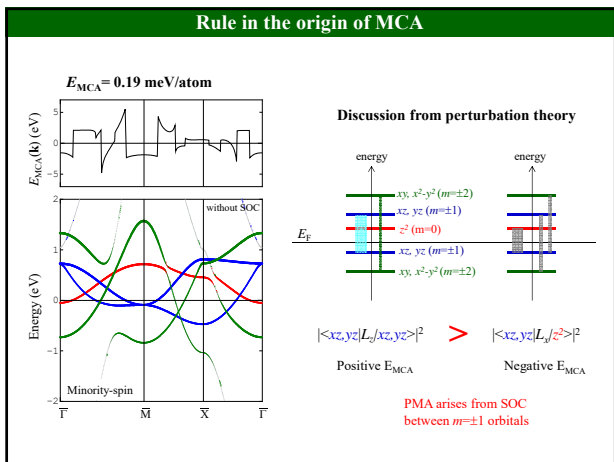
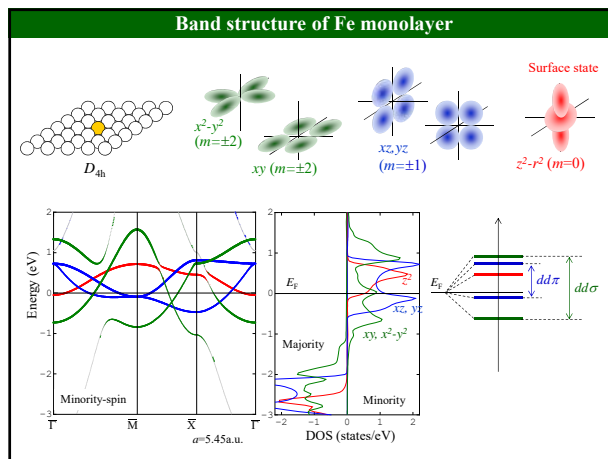
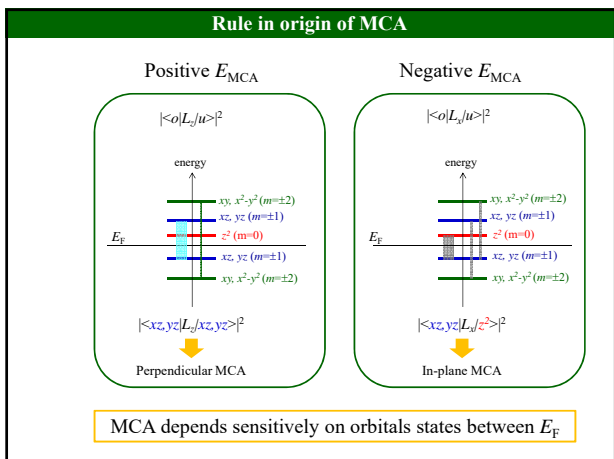
Na : $1s^2 2s^2 2p^6 3s$

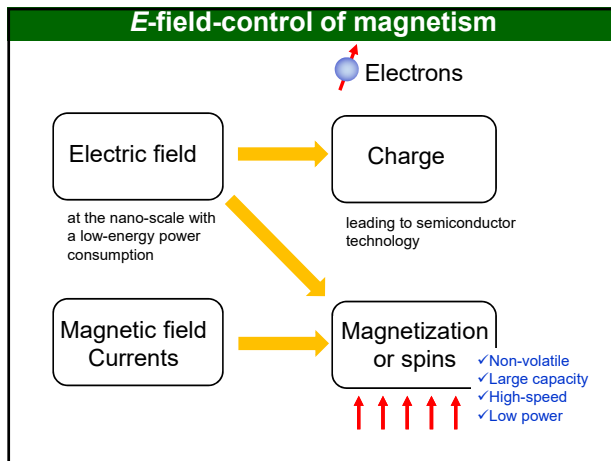
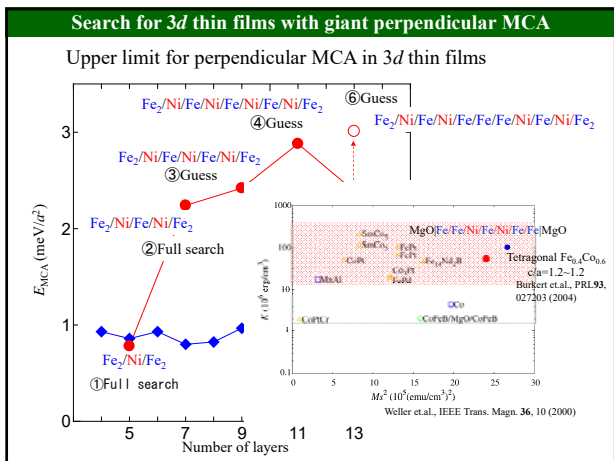
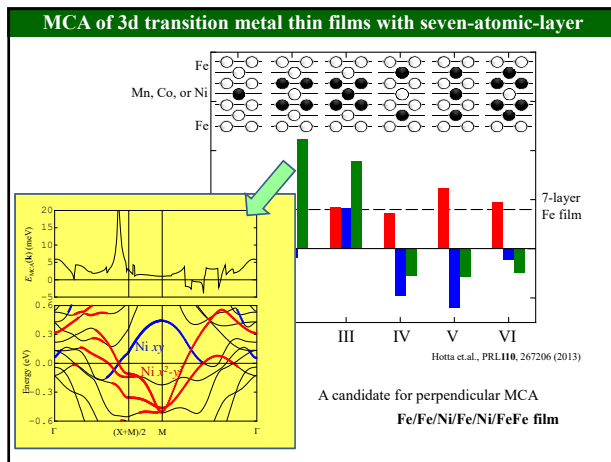
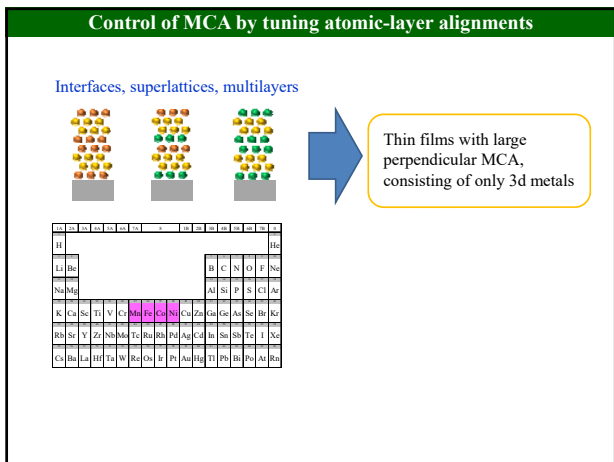
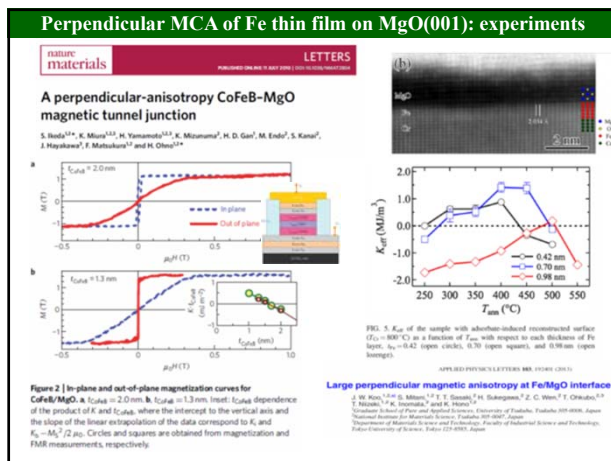
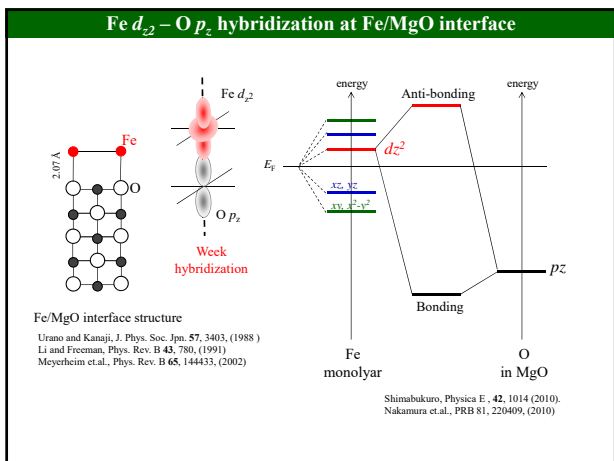
K : $1s^2 2s^2 2p^6 3s^2 3p^6 4s$

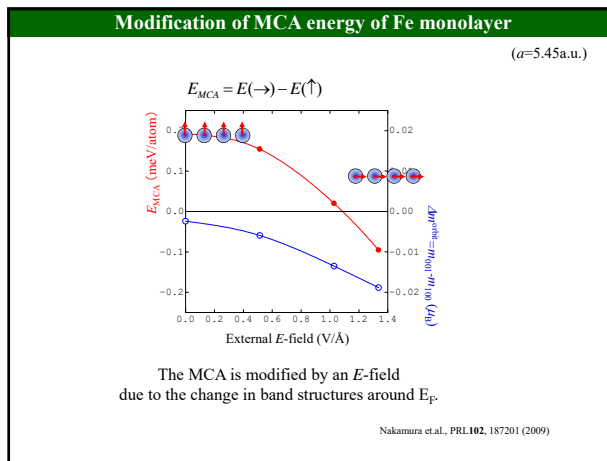
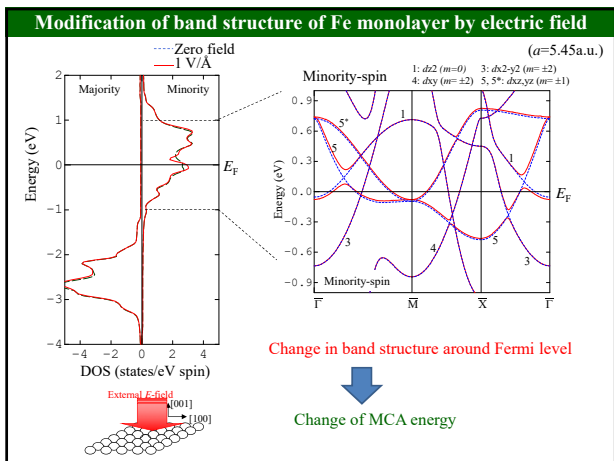
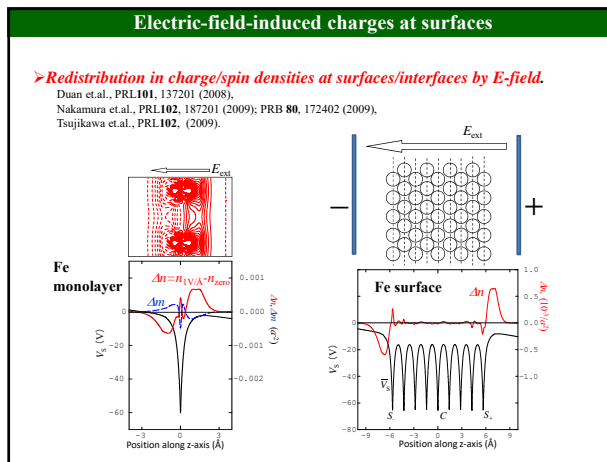
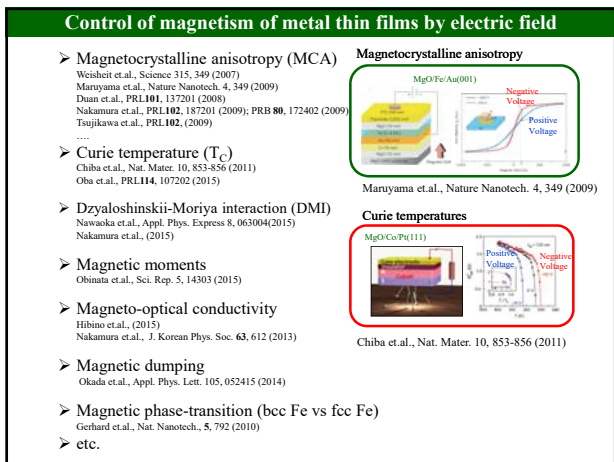
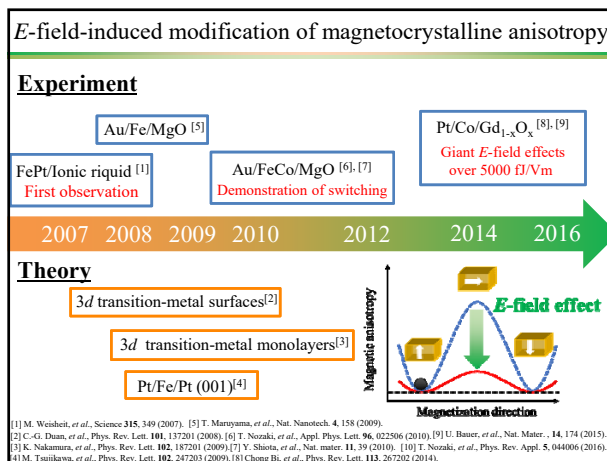
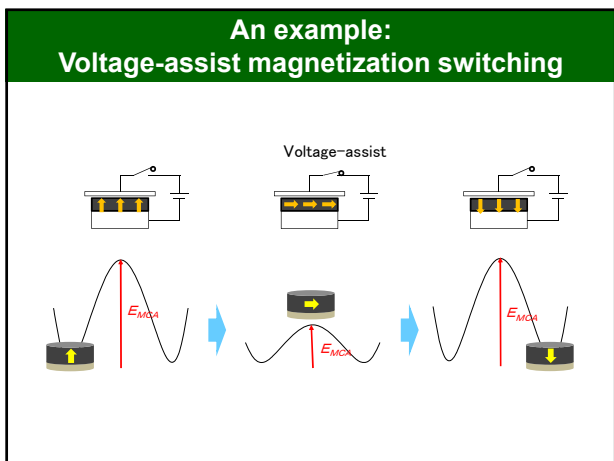
Atomic core

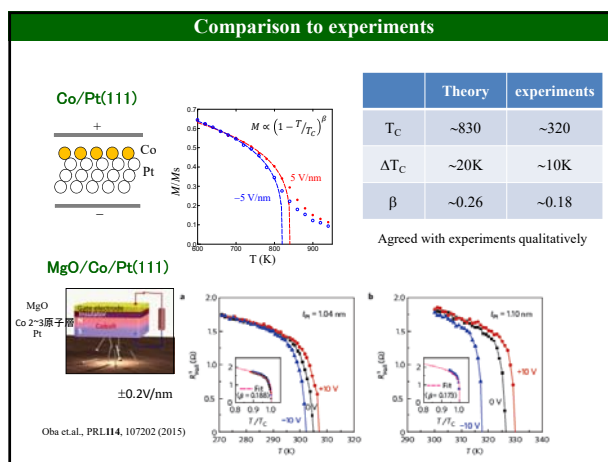
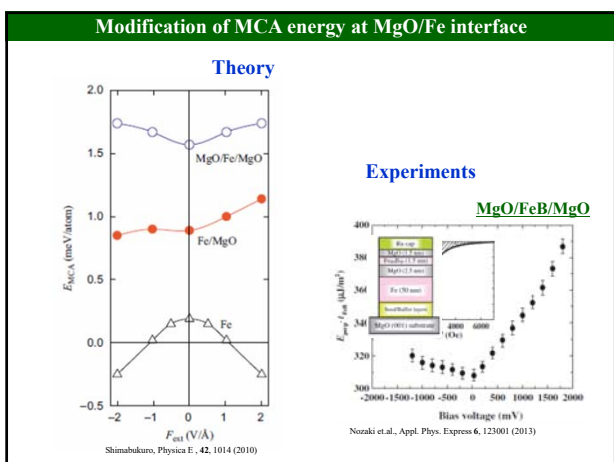












Summary

Artificial multilayer thin-films

magnetic properties

- ✓ Perpendicular magnetization
- ✓ Tunnel magneto resistance
- ✓ Spin current and torque
- ✓ etc.

Importance of understanding electronic structures

Key ideas for PMCA

- Interface-induced PMCA
- Atomic-layer-alignment-tuned PMA (artificial multilayers)

- Crystal structures and atomic arrangements
- The number of valence electrons
- Eigenvalues and eigenstates of s, p, d, f orbitals
- d-d (d-sp) hybridization